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Form PTO-1449 (REV. 1/06)		US Dept. of Commerce PATENT & TRADEMARK OFFICE		ATTY DOCKET NO. A3316-US-NP	APPLICATION NO. 10/625,811
INFORMATION DISCLOSURE STATEMENT (Use several sheets if necessary)				APPLICANT(S) Christopher L. Chua	
				FILING DATE 7/23/2003	GROUP 2828
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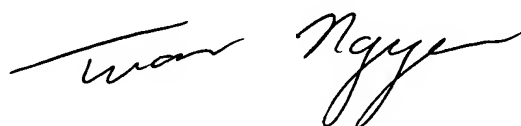
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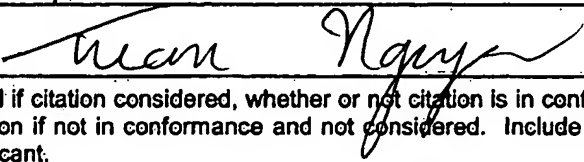
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